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(54) Title: TUNGSTEN GATES FOR NON-PLANAR TRANSISTORS

(57) Abstract: The present description relates to the field of fabricating micro-electronic devices having non-planar transistors. Embodiments of the present description relate to the formation of gates within non-planar NMOS transistors, wherein an NMOS work-function material, such as a composition of aluminum, titanium, and carbon, may be used in conjunction with a titanium-containing gate fill barrier to facilitate the use of a tungsten-containing conductive material in the formation of a gate electrode of the non-planar NMOS transistor gate.

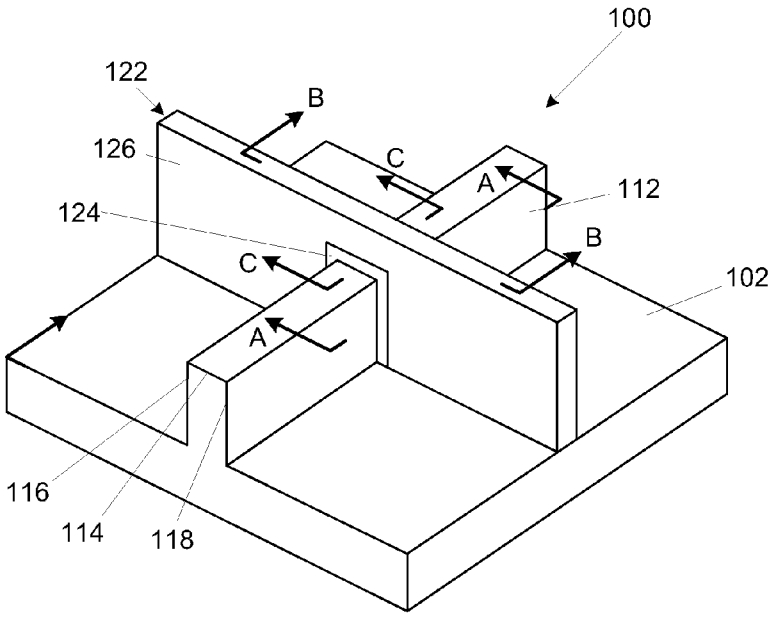



FIG. 1

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